MEMORY **Un-buffered** $1 \text{ M} \times 64 \text{ BIT}$ SYNCHRONOUS DYNAMIC RAM SO-DIMM

MB8501S064AC-100/-84/-67

168-pin, 1 Clock, 1-bank, based on 1 $M \times 16$ BIT SDRAMs with SPD

DESCRIPTION

The Fujitsu MB8501 S064AB is a fully decoded, CMOS Synchronous Dynamic Random Access Memory (SDRAM) Module consisting of four MB811161622A devices which organized as two banks of 1 M × 16 bits and a 2 K-bit serial EEPROM on a 168-pin glass-epoxy substrate.

The MB8501S064AB features a fully synchronous operation referenced to a positive edge clock whereby all operations are synchronized at a clock input which enables high performance and simple user interface coexistence.

The MB8501S064AB is optimized for those applications requiring high speed, high performance and large memory storage, and high density memory organizations.

This module is ideally suited for workstations, PCs, laser printers, and other applications where a simple interface is needed.

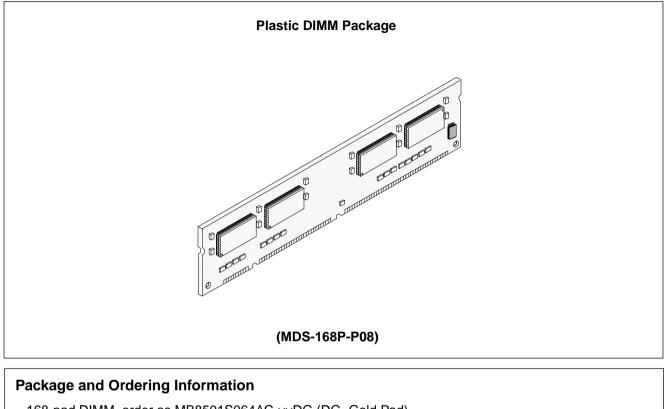
PRODUCT LINE & FEATURES

| Para | ameter | MB8501S064AC-100 | MB8501S064AC-84 | MB8501S064AC-67 |
|-------------------------|-----------------|--|--|--|
| Clock Frequency | | 100 MHz max. | 84 MHz max. | 67 MHz max. |
| Burst Mode Cycle Time | | 10 ns max. (CL = 3) 15 ns max. (CL = 2) | 12 ns max. (CL = 3) 17 ns max. (CL = 2) | 15 ns max. (CL = 3) 20 ns max. (CL = 2) |
| RAS Access Time | | 54 ns max. | 56 ns max. | 60 ns max. |
| CAS Access Time | CAS Access Time | | 26 ns max. | 30 ns max. |
| Output Valid from Clock | | 8.5 ns max. (CL = 3) 9 ns max. (CL = 2) | 8.5 ns max. (CL = 3) 9 ns max. (CL = 2) | 9 ns max. (CL = 3) 10 ns max. (CL = 2) |
| Power Burst Mode | | 1944 mW max. | 1800 mW max. | 1620 mW max. |
| Dissipation | Power Down Mode | | 28.8 mW max. | |

- Un-buffered 168-pin DIMM Socket Type (Lead pitch: 1.27 mm)
- Conformed to JEDEC Standard (1 CLK)
- Organization: 1,048,576 words × 64 bits
- 3.3 V ±0.3 V Supply Voltage
- All input/output LVTTL compatible

- 2048 Refresh Cycle every 32.8 ms
- Auto and Self Refresh
- CKE Power Down Mode
- DQM Byte Masking (Read/Write)
- Memory : MB811171622A (1 M×16, 2-bank)×4 pcs. Serial Presence Detect (SPD) with Serial EEPROM
 - Module size: 1.0" (height) \times 5.25" (length) \times 0.110" (thick)

PACKAGE



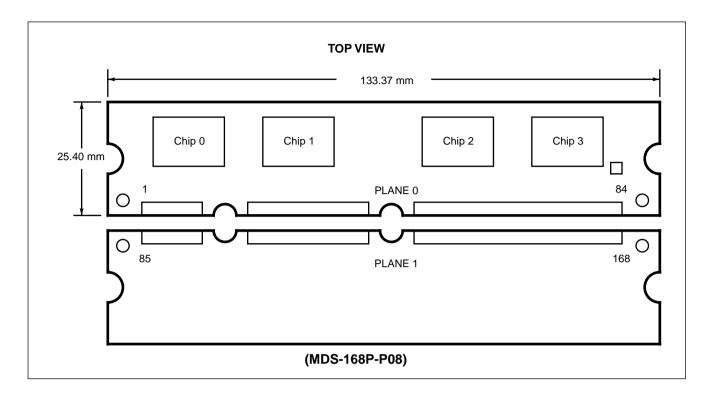
- 168-pad DIMM, order as MB8501S064AC-xxDG (DG=Gold Pad)

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MB8501S064AC-100/-84/-67

■ PIN ASSIGNMENTS

| Pin No. | Signal Name | Pin No. | Signal Name | Pin No. | Signal Name | Pin No. | Signal Name | Pin No. | Signal Name | Pin No. | Signal Name |
|------------|-------------------|------------|-------------------|------------|------------------|------------|-------------------|------------|-------------------|------------|------------------|
| 1 | Vss | 29 | DQMB ₁ | 57 | DQ18 | 85 | Vss | 113 | DQMB₅ | 141 | DQ50 |
| 2 | DQ ₀ | 30 | \overline{CS}_0 | 58 | DQ ₁₉ | 86 | DQ32 | 114 | N.C. | 142 | DQ ₅₁ |
| 3 | DQ ₁ | 31 | N.C. | 59 | Vcc | 87 | DQ33 | 115 | RAS | 143 | Vcc |
| 4 | DQ ₂ | 32 | Vss | 60 | DQ20 | 88 | DQ ₃₄ | 116 | Vss | 144 | DQ ₅₂ |
| 5 | DQ₃ | 33 | Ao | 61 | N.C. | 89 | DQ ₃₅ | 117 | A ₁ | 145 | N.C. |
| 6 | Vcc | 34 | A2 | 62 | N.C. | 90 | Vcc | 118 | Аз | 146 | N.C. |
| 7 | DQ4 | 35 | A4 | 63 | N.C. | 91 | DQ ₃₆ | 119 | A ₅ | 147 | N.C. |
| 8 | DQ₅ | 36 | A6 | 64 | Vss | 92 | DQ ₃₇ | 120 | A7 | 148 | Vss |
| 9 | DQ ₆ | 37 | A ₈ | 65 | DQ ₂₁ | 93 | DQ38 | 121 | A9 | 149 | DQ ₅₃ |
| 10 | DQ7 | 38 | A10 | 66 | DQ22 | 94 | DQ39 | 122 | A11 | 150 | DQ ₅₄ |
| 11 | DQ8 | 39 | N.C. | 67 | DQ ₂₃ | 95 | DQ ₄₀ | 123 | N.C. | 151 | DQ55 |
| 12 | Vss | 40 | Vcc | 68 | Vss | 96 | Vss | 124 | Vcc | 152 | Vss |
| 13 | DQ ₉ | 41 | Vcc | 69 | DQ ₂₄ | 97 | DQ ₄₁ | 125 | N.C. | 153 | DQ ₅₆ |
| 14 | DQ ₁₀ | 42 | CLK ₀ | 70 | DQ ₂₅ | 98 | DQ ₄₂ | 126 | N.C. | 154 | DQ ₅₇ |
| 15 | DQ ₁₁ | 43 | Vss | 71 | DQ ₂₆ | 99 | DQ ₄₃ | 127 | Vss | 155 | DQ ₅₈ |
| 16 | DQ12 | 44 | N.C. | 72 | DQ ₂₇ | 100 | DQ44 | 128 | CKE | 156 | DQ59 |
| 17 | DQ ₁₃ | 45 | \overline{CS}_2 | 73 | Vcc | 101 | DQ ₄₅ | 129 | N.C. | 157 | Vcc |
| 18 | Vcc | 46 | DQMB ₂ | 74 | DQ ₂₈ | 102 | Vcc | 130 | DQMB ₆ | 158 | DQ60 |
| 19 | DQ ₁₄ | 47 | DQMB ₃ | 75 | DQ29 | 103 | DQ ₄₆ | 131 | DQMB7 | 159 | DQ ₆₁ |
| 20 | DQ ₁₅ | 48 | N.C. | 76 | DQ30 | 104 | DQ ₄₇ | 132 | N.C. | 160 | DQ ₆₂ |
| 21 | N.C. | 49 | Vcc | 77 | DQ ₃₁ | 105 | N.C. | 133 | Vcc | 161 | DQ ₆₃ |
| 22 | N.C. | 50 | N.C. | 78 | Vss | 106 | N.C. | 134 | N.C. | 162 | Vss |
| 23 | Vss | 51 | N.C. | 79 | N.C. | 107 | Vss | 135 | N.C. | 163 | N.C. |
| 24 | N.C. | 52 | N.C. | 80 | N.C. | 108 | N.C. | 136 | N.C. | 164 | N.C. |
| 25 | N.C. | 53 | N.C. | 81 | N.C. | 109 | N.C. | 137 | N.C. | 165 | SA ₀ |
| 26 | Vcc | 54 | Vss | 82 | SDA | 110 | Vcc | 138 | Vss | 166 | SA1 |
| 27 | WE | 55 | DQ ₁₆ | 83 | SCL | 111 | CAS | 139 | DQ ₄₈ | 167 | SA ₂ |
| 28 | DQMB ₀ | 56 | DQ ₁₇ | 84 | Vcc | 112 | DQMB ₄ | 140 | DQ ₄₉ | 168 | Vcc |



■ PIN DESCRIPTION

| Symbol | I/O | Function | Symbol | I/O | Function |
|--|-----|-----------------------|-------------------------------------|-----|--|
| A ₀ to A ₁₁ | I | Address Input | DQ ₀ to DQ ₆₃ | | Data Input/Data Output |
| RAS | I | Row Address Strobe | Vcc | I/O | Power Supply (+3.3 V) |
| CAS | I | Column Address Strobe | Vss | - | Ground (0 V) |
| WE | I | Write Enable | N.C. | - | No Connection |
| DQMB ₀ to DQMB ₇ | I | Data (DQ) Mask | SA ₀ to SA ₂ | - | Serial PD Address Input |
| CLK₀ | I | Clock Input | SCL | I | Serial PD Clock |
| СКЕ | I | Clock Enable | SDA | I/O | Serial PD Address/Data Input/Output |
| $\overline{CS}_0, \overline{CS}_2$ | I | Chip Select | | | |

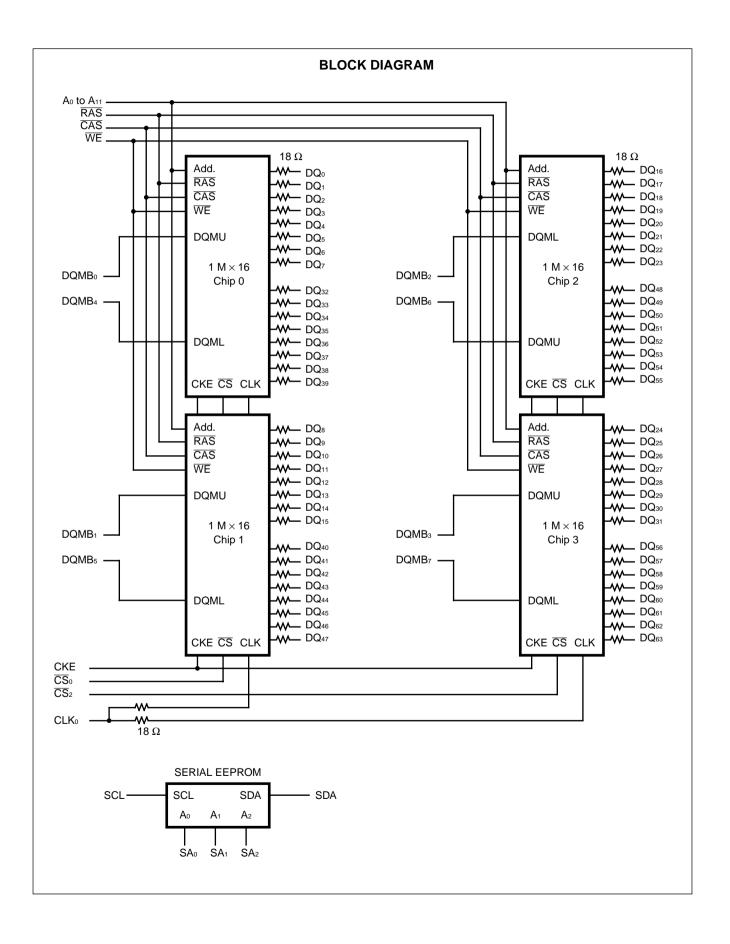
SERIAL-PD INFORMATION

| Byte | Function Described | | Bit7 | Bit6 | Bit5 | Bit4 | Bit3 | Bit2 | Bit1 | Bit0 |
|-----------|--------------------------------------|------------|------|------|------|------|------|------|------|------|
| 0 | Defines Number of Bytes Written into | 128 Byte | 1 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| | Serial Memory at Module Manufacture | - | | | | | | | | |
| 1 | Total Number of Bytes of SPD Memory | 256 Byte | 0 | 0 | 0 | 0 | 1 | 0 | 0 | 0 |
| 2 3 | Fundamental Memory Type | SDRAM | 0 | 0 | 0 | 0 | 0 | 1 | 0 | 0 |
| 3 | Number of Row Addresses | 11 | 0 | 0 | 0 | 0 | 1 | 0 | 1 | 1 |
| 4 | Number of Column Addresses | 8 | 0 | 0 | 0 | 0 | 1 | 0 | 0 | 0 |
| 5 | Number of Module Banks | 1 bank | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 1 |
| 6 | Data Width | 64 bit | 0 | 1 | 0 | 0 | 0 | 0 | 0 | 0 |
| 7 | Data Width (Continuation) | +0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| 8 | Interface Type | LVTTL | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 1 |
| 9 | SDRAM Cycle Time | 10 ns | 1 | 0 | 1 | 0 | 0 | 0 | 0 | 0 |
| | | 12 ns | 1 | 1 | 0 | 0 | 0 | 0 | 0 | 0 |
| | | 15 ns | 1 | 1 | 1 | 1 | 0 | 0 | 0 | 0 |
| 10 | SDRAM Access from Clock | 8.5 ns | 1 | 0 | 0 | 0 | 0 | 1 | 0 | 1 |
| | | 9 ns | 1 | 0 | 0 | 1 | 0 | 0 | 0 | 0 |
| 11 | DIMM Configuration Type | Non-Parity | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| 12 | Refresh Rate/Type | Self, Norm | 1 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| 13 | SDRAM Module Attributes | UN-Buffer | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| 14 | SDRAM Device Attributes | (*) | 0 | 0 | 0 | 0 | 0 | 1 | 1 | 0 |
| 15 | Minimum Clock Delay Back to Back | 1 Cycle | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 1 |
| | Random Column Address | | | - | - | - | | | | |
| 16 | Burst Lengths Supported | 1, 2, 4, 8 | 0 | 0 | 0 | 0 | 1 | 1 | 1 | 1 |
| 17 | Number of Banks on Each SDRAM Device | 2 bank | 0 | 0 | 0 | 0 | 0 | 0 | 1 | 0 |
| 18 | CAS Latency | 2, 3 | 0 | 0 | 0 | 0 | 0 | 1 | 1 | 0 |
| 19 | CS Latency | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | |
| 20 | Write Latency | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 1 |
| 21 to 31 | Reserved for Future Offerings | — | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| 32 to 63 | Superset Information | — | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| 64 to 125 | Manufacturer's Information | | 0 | 0 | 0 | 0 | 0 | 0 | 0 | 0 |
| 126 | Intel Specification Frequency | 66 MHz | 0 | 1 | 1 | 0 | 0 | 1 | 1 | 0 |
| 127 | Intel Specification CAS Latency | 2, 3 | 0 | 0 | 0 | 0 | 0 | 1 | 1 | 0 |
| 128+ | Unused Storage Locations | _ | - | _ | - | - | _ | _ | - | - |

Note: Any write operation must NOT be executed into the addresses of Byte 0 to Byte 127. Some or all data stored into Byte 0 to Byte 127 may be broken.

(*) Byte 14 : SDRAM Device Attributes

| Bit7 | Bit6 | Bit5 | Bit4 | Bit3 | Bit2 | Bit1 | Bit0 |
|------|------|------|------|--|-------------------------------|---------------------------------|-------------------------------------|
| TBD | TBD | TBD | TBD | Supported Single Write/ Burst Read | Supported Precharge All | Supported Auto- Precharge | Supported Early RAS Precharge |
| 0 | 0 | 0 | 0 | 0 | 1 | 1 | 0 |



■ ABSOLUTE MAXIMUM RATINGS (See WARNING)

| Baramatar | Symbol | Va | Value | | | |
|-----------------------|--------|------|-------|------|--|--|
| Parameter | Symbol | Min. | Max. | Unit | | |
| Supply Voltage* | Vcc | -0.5 | +4.6 | V | | |
| Input Voltage* | Vin | -0.5 | +4.6 | V | | |
| Output Voltage* | Vout | -0.5 | +4.6 | V | | |
| Storage Temperature | Тѕтс | -55 | +125 | °C | | |
| Power Dissipation | PD | | 5.2 | W | | |
| Output Current (D.C.) | Ιουτ | -50 | +50 | mA | | |

* : Voltages referenced to Vss (= 0 V)

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

| Parameter | Notes | Symbol | | Unit | | |
|--------------------------------|-------|--------|------|------|----------|------|
| Farameter | Notes | Symbol | Min. | Тур. | Max. | Unit |
| Supply Voltage | *1 | Vcc | 3.0 | 3.3 | 3.6 | V |
| Supply voltage | I | Vss | 0 | 0 | 0 | V |
| Input High Voltage, All Inputs | *1 | Vін | 2.0 | | Vcc +0.5 | V |
| Input Low Voltage, All Inputs | *1, 2 | VIL | -0.5 | | 0.8 | V |
| Ambient Temperature | | TA | 0 | _ | +70 | °C |

*1. Voltages referenced to Vss (= 0 V)

*2. $V_{\mathbb{L}}$ (min) = -1.5 V AC (Pulse Width \leq 5 ns)

WARNING: Recommended operating conditions are normal operating ranges for the semiconductor device. All the device's electrical characteristics are warranted when operated within these ranges.

Always use semiconductor devices within the recommended operating conditions. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses , operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representative beforehand.

■ CAPACITANCE

| | +3.3 V, f = 1 MHz, TA | $= +25^{\circ}C$ |
|--|-----------------------|------------------|
|--|-----------------------|------------------|

| Parame | or | Symbol | Va | lue | Unit |
|--------------------------|--|--------|------|------|------|
| Falalle | lei | Symbol | Min. | Max. | Unit |
| | A ₀ to A ₁₁ | CIN1 | — | 30 | pF |
| | RAS, CAS, WE | CIN2 | — | 29 | pF |
| | $\overline{CS}_0, \overline{CS}_2$ | Сімз | — | 15 | pF |
| | CKE | CIN4 | — | 29 | pF |
| Input Capacitance | | CIN5 | — | 29 | pF |
| | DQMB ₀ to DQMB ₇ | CIN6 | — | 11 | pF |
| | SCL | CSCL | — | 6 | pF |
| | SA0, SA1, SA2 | CSA | — | 5 | pF |
| | SDA | CSDA | — | 6 | pF |
| Input/Output Capacitance | DQ ₀ to DQ ₆₃ | CDQ | | 11 | pF |

■ DC CHARACTERISTICS

(At recommended operating conditions unless otherwise noted.)

| Denemoter | Nataa | | Ourseland | O a malitia m | Va | lue | 11 |
|--|--------|------------------|--|--|------|------|------|
| Parameter | Notes | | Symbol | Condition | Min. | Max. | Unit |
| | | MB8501S064AC-100 | | No Burst; | | 340 | mA |
| | | MB8501S064AC-84 | Icc1s | tcκ = min t _{RC} = min | | 320 | mA |
| Operating Current (Average Power | *2 | MB8501S064AC-67 | | One Bank Active | | 300 | mA |
| Supply Current) | | MB8501S064AC-100 | | No Burst; | | 520 | mA |
| | | MB8501S064AC-84 | Ісс1р | tск = min trc = min | | 480 | mA |
| | | MB8501S064AC-67 | - | All Banks Active | | 440 | mA |
| Precharge Standby Current (Power | *0 | | Ісс2р | CKE = V⊩, tcĸ = min All Banks Idle | | 8 | mA |
| Supply Current) | | | Ісс2N | CKE = V⊮, tcк = min All Banks Idle | | 120 | mA |
| Active Standby Current (Power *2 Supply Current) | | | Іссзр | CKE = V⊫, tcк = min Any Bank Active | | 120 | mA |
| | | | Іссзи | CKE = V⊮, tcк = min Any Bank Active | | 200 | mA |
| Burst Mode Current | | MB8501S064AC-100 | | | _ | 540 | mA |
| (Average Power | *2 | MB8501S064AC-84 | Icc4 | tcк = min | _ | 500 | mA |
| Supply Current) | | MB8501S064AC-67 | | | | 460 | mA |
| Auto-refresh Current | | MB8501S064AC-100 | | Auto Refresh | | 440 | mA |
| (Average Power | *2 | MB8501S064AC-84 | Icc5 | tск = min t _{RC} = min | | 400 | mA |
| Supply Current) | | MB8501S064AC-67 | | t _{RRD} = min | | 360 | mA |
| Self-refresh Current (Average Power Supply | Currer | nt) | Icc6 | tcк = VIL | | 8 | mA |
| Input Leakage Current (All Inputs) | | lı (l) | $\begin{array}{l} 0 \ V \leq V_{IN} \leq V_{CC} \\ \text{All other pins not} \\ \text{under test} = 0 \ V \\ 3.0 \ V \leq V_{CC} \leq 3.6 \ V \end{array}$ | -30 | 30 | μA | |
| Output Leakage Current | | IO (L) | $\begin{array}{l} Output \mbox{ is disabled (Hi-Z)} \\ 0 \ V \leq V_{OUT} \leq V_{CC} \\ 3.0 \ V \leq V_{CC} \leq 3.6 \ V \end{array}$ | -10 | 10 | μA | |
| LVTTL Output High Voltage | *1 | | Vон | lон = −2.0 mA | 2.4 | _ | V |
| LVTTL Output Low Voltage | *1 | | Vol | IoL = +2.0 mA | | 0.4 | V |

Notes: *1. Voltages referenced to Vss (= 0 V)

*2. Icc depends on the output termination, load conditions, clock cycle rate and signal clock rate. The specified values are obtained with the output open and no termination register.

*3. An initial pause (DESL on NOP) of 200 μs is required after power-on followed by a minimum of eight Auto-Refresh cycles.

*4. DC characteristics is the Serial PD standby state ($V_{IN} = GND$ or V_{CC}).

■ AC CHARACTERISTICS

(1) BASE CHARACTERISTICS

(At recommended operating conditions unless otherwise noted.)

| No. | Parameter Notes | | Symbol | | S064AC 00 | | S064AC 34 | MB8501S064AC -67 | | Unit |
|-----|-----------------------------------|--------|--------------|------|--------------|------|--------------|---------------------|------|------|
| | | | | Min. | Max. | Min. | Max. | Min. | Max. | |
| 1 | Clock Period | CL = 3 | 4 | 10 | — | 12 | | 15 | _ | ns |
| I | Clock Period | CL = 2 | tск | 15 | | 17 | | 20 | _ | ns |
| 2 | Clock High Time | | tсн | 4 | | 4 | | 4 | _ | ns |
| 3 | Clock Low Time | | tc∟ | 4 | | 4 | | 4 | — | ns |
| 4 | CS Set Up Time | | tsc | 3 | | 3 | | 3 | _ | ns |
| 5 | CS Hold Time | | tнc | 1 | | 1 | | 1 | _ | ns |
| 6 | Input Set Up Time | | tsi | 3 | | 3 | | 3 | — | ns |
| 7 | Input Hold Time | | tнı | 1 | | 1 | | 1 | — | ns |
| 8 | Data Input Set Up Time | | tsid | 3 | | 3 | | 3 | — | ns |
| 9 | Data Input Hold Time | | tнid | 1 | — | 1 | | 1 | — | ns |
| | Output Valid | CL = 3 | | | 8.5 | _ | 8.5 | | 9 | |
| 10 | from Clock *1, *2 (tcLK = min) | CL = 2 | tac | | 9 | _ | 9 | _ | 10 | ns |
| 11 | Output in Low-Z | | tolz | 3 | | 3 | | 3 | _ | ns |
| 12 | Output in High-Z *3 | | tонz | 3 | | 3 | | 3 | _ | ns |
| 13 | Output Hold Time | | tон | 3 | _ | 3 | | 3 | _ | ns |
| 14 | Time between Refresh | | tref | | 32.8 | _ | 32.8 | | 32.8 | ms |
| 15 | Transition Time | | tτ | 0.5 | 2 | 0.5 | 2 | 0.5 | 2 | ns |
| 16 | Power Down Exit Time | | t PDE | 3 | _ | 4 | _ | 5 | _ | ns |

| No. | Parameter | Notes | Symbol | MB8501S064AC -100 | | MB8501S064AC -84 | | MB8501S064AC -67 | | Unit |
|-----|-----------------------------------|--------|--------------|----------------------|--------|---------------------|--------|---------------------|--------|------|
| | | | - | Min. | Max. | Min. | Max. | Min | Max. | |
| 1 | RAS Cycle Time | *4 | t RC | 90 | | 100 | | 110 | | ns |
| 2 | RAS Access Time | *5 | t RAC | | 54 | | 56 | — | 60 | ns |
| 3 | CAS Access Time | *6, *9 | tcac | | 24 | | 26 | | 30 | ns |
| 4 | RAS Precharge Time | | t RP | 30 | | 35 | — | 40 | — | ns |
| 5 | RAS Active Time | | tras | 60 | 100000 | 65 | 100000 | 70 | 100000 | ns |
| 6 | RAS to CAS Delay Time | *7 | t RCD | 30 | — | 30 | _ | 30 | — | ns |
| 7 | Write Recovery Time | | t wr | 10 | _ | 12 | _ | 15 | — | ns |
| 8 | Write Precharge Time | | t RWL | 10 | | 12 | _ | 15 | — | ns |
| 9 | RAS to CAS Bank Active Delay Time | | t rrd | 30 | _ | 30 | _ | 30 | _ | ns |

(2) BASE VALUES FOR CLOCK COUNT/LATENCY

(3) CLOCK COUNT FORMULA (*8)

 $Clock \ge \frac{Base Value}{Clock Period}$ (Round off a whole number)

(4) LATENCY (The latency values on these parameters are fixed regardless of clock period.)

| | | | | - | - | - | _ |
|-----|--|--------|--------|----------------------|---------------------|---------------------|-------|
| No. | Parameter | | Symbol | MB8501S064AC -100 | MB8501S064AC -84 | MB8501S064AC -67 | Unit |
| 1 | CKE to Clock Disable | | Іске | 1 | 1 | 1 | Cycle |
| 2 | DQM to Output in High-Z | | ldqz | 2 | 2 | 2 | Cycle |
| 3 | DQM to Input Data Delay | | IDQD | 0 | 0 | 0 | Cycle |
| 4 | Last Output to Write Command Delay | | lowd | 2 | 2 | 2 | Cycle |
| 5 | Write Command to Input Data Delay | | ldwd | 0 | 0 | 0 | Cycle |
| 6 | Precharge to Output in High-Z Delay | CL = 3 | la au | 3 | 3 | 3 | Cycle |
| | | CL = 2 | IROH | 2 | 2 | 2 | Cycle |
| 7 | Mode Register Access to Bank Active (min) | | Imrd | 2 | 2 | 2 | Cycle |
| 8 | \overline{CAS} to \overline{CAS} Delay (min) | | Ісср | 1 | 1 | 1 | Cycle |
| 9 | CAS Bank Delay (min) | | Свр | 1 | 1 | 1 | Cycle |

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MB8501S064AC-100/-84/-67

- Notes: *1. Assumes tRCD and tCAC are satisfied.
 - *2. tac also specifies the access time at burst mode except for first access.
 - *3. Specified where output buffer is no longer driven.
 - *4. Actual clock count of trc (Irc) will be sum of clock count of tras (Iras) and trp (Irp).
 - *5. trac is a reference value. Maximum value is obtained from the sum of trcd (min) and tcac (max).
 - *6. Assumes trac and tac are satisfied.
 - *7. Operation within the tRCD (min) ensures that tRAC can be met; if tRCD is greater than the specified tRCD (min), access time is determined by tCAC and tAC.
 - *8. All base values are measured from the clock edge at the command input to the clock edge for the next command input.

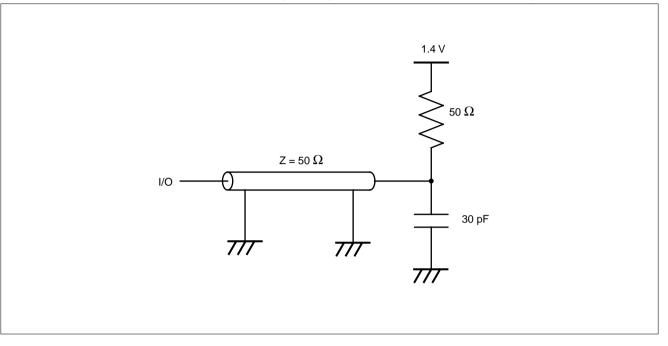
All clock counts are calculated by a simple formula:

clock count equals base value divided by clock period (round off to a whole number).

- *9. The ICAC (CAS latency: CL) is programmed by the mode register.
- *10. An initial pause (DESL on NOP) of 200 μs is required after power-up followed by a minimum of eight Auto-Refresh cycles.
- *11. 1.4 V or V_{REF} is the reference level for measuring timing of signals. Transition times are measured between V_{IH} (min) and V_{IL} (max).
- *12. AC characteristics assume $t_T = 1$ ns and 30 pF of capacitive load.

*Source: See MB811171622A Data Sheet for details on the electricals.

■ AC OPERATING TEST CONDITION (Example of AC Test Load Circuit)



■ SERIAL PRESENCE DETECT(SPD) FUNCTION

1. PIN DESCRIPTIONS

SCL (Serial Clock)

SCL input is used to clock all data input/output of SPD

SDA (Serial Data)

SDA is a common pin used for all data input/output of SPD. The SDA pull-up resistor is required due to the open-drain output.

SA₀, SA₁, SA₂ (Address)

Address inputs are used to set the least significant three bits of the eight bits slave address. The address inputs must be fixed to select a particular module and the fixed address of each module must be different each other.

2. SPD OPERATIONS

CLOCK and DATA CONVENTION

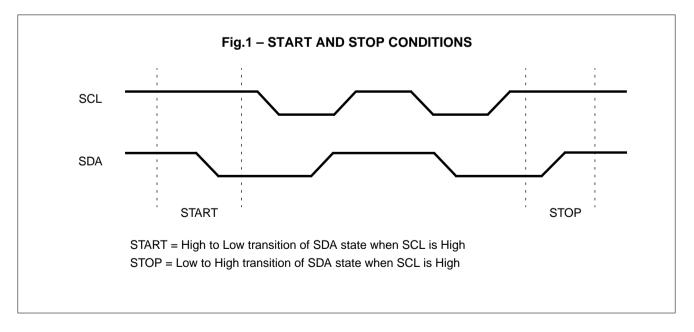
Data states on the SDA can change only during SCL=Low. SDA state changes during SCL=High are indicated start and stop conditions. Refer to Fig.1 below.

START CONDITION

All commands are preceded by a start condition, which is a transition of SDA state from High to Low when SCL=High. SPD will not respond to any command until this condition has been met.

STOP CONDITION

All read or write operation must be terminated by a stop condition, which is a transition of SDA state from Low to High when SCL=High. The stop condition is also used to make the SPD into the state of standby power mode after a read sequence.



ACKNOWLEDGE

Acknowledge is a software convention used to indicate successful data transfer. The transmitting device, either master or slave, will release the bus after transmitting eight bits. During the ninth clock cycle the receiver will put the SDA line to Low in order to acknowledge that it received the eight bits of data.

The SPD will respond with an acknowledge when it received the start condition followed by slave address issued by master.

In the read operation, the SPD will transmit eight bits of data, release the SDA line and monitor the line for an acknowledge. If an acknowledge is detected and no stop condition is issued by master, the SPD will continue to transmit data. If an acknowledge is not detected, the SPD will terminated further data transmissions. The master must then issue a stop condition to return the SPD to the standby power mode.

In the write operation, upon receipt of eight bits of data the SPD will respond with an acknowledge, and await the next eight bits of data, again responding with an acknowledge until the stop condition is issued by master.

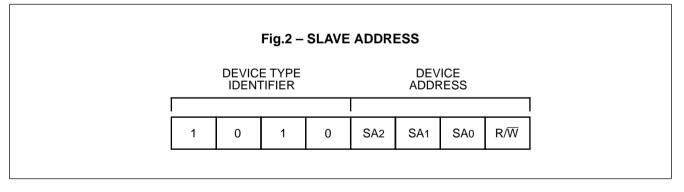
SLAVE ADDRESS ADDRESSING

Following a start condition, the master must output the eight bits slave address. The most significant four bits of the slave address are device type identifier. For the SPD this is fixed as 1010[B]. Refer to the Fig.2 below.

The next three significant bits are used to select a particular device. A system could have up to eight SPD devices–namely up to eight modules–on the bus. The eight addresses for eight SPD devices are defined by the state of the SA₀, SA₁ and SA₂ inputs.

The last bit of the slave address defines the operation to be performed. When R/\overline{W} bit is "1", a read operation is selected, when R/\overline{W} bit is "0", a write operation is selected.

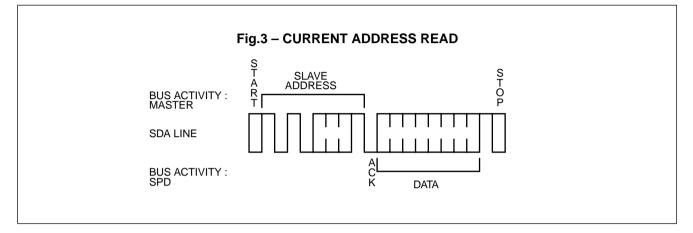
Following the start condition, the SPD monitors the SDA line comparing the slave address being transmitted with its slave address (device type and state of SA₀, SA₁, and SA₂ inputs). Upon a correct compare the SPD outputs an acknowledge on the SDA line. Depending on the state of the R/\overline{W} bit, the SPD will execute a read or write operation.



3. READ OPERATION

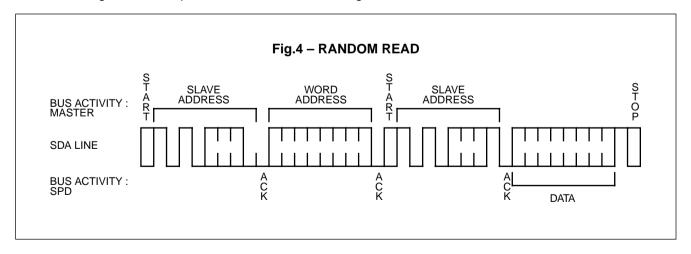
CURRENT ADDRESS READ

Internally the SPD contains an address counter that maintains the address of the last data accessed, incremented by one. Therefore, if the last access (either a read or write operation) was to address(n), the next read operation would access data from address(n+1). Upon receipt of the slave address with the R/\overline{W} bit = "1", the SPD issues an acknowledge and transmits the eight bits of data during the next eight clock cycles. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig.3 for the sequence of address, acknowledge and data transfer.



RANDOM READ

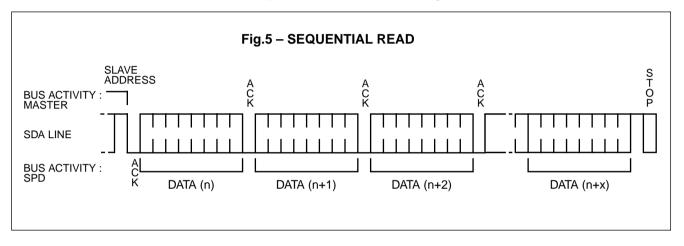
Random Read operations allow the master to access any memory location in a random manner. Prior to issuing the slave address with the R/W bit = "1", the master must first perform a "dummy" write operation on the SPD. The master issues the start condition, and the slave address followed by the word address. After the word address acknowledge, the master immediately reissues the start condition and the slave address with the R/ \overline{W} bit = "1". This will be followed by an acknowledge from the SPD and then by the eight bits of data. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig.4 for the sequence of address, acknowledge and data transfer.



SEQUENTIAL READ

Sequential Read can be initiated as either a current address read or random read. The first data are transmitted as with the other read mode, however, the master now responds with an acknowledge, indicating it requires additional data. The SPD continues to output data for each acknowledge received. The master terminates this transmission by issuing a stop condition, omitting the ninth clock cycle acknowledge. Refer to Fig.5 for the sequence of address, acknowledge and data transfer.

The data output is sequential, with the data from address(n) followed by the data from address(n+1). The address counter for read operations increments all address bits, allowing the entire memory contents to be serially read during one operation. At the end of the address space (address 255), the counter "rolls over" to address 0 and the SPD continues to output data for each acknowledge received.



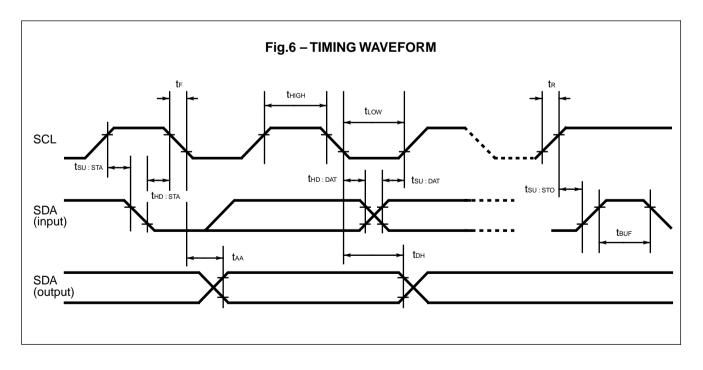
4. DC CHARACTERISTICS

| Parameter | Note | Symbol | Condition | Value | | Unit |
|------------------------|------|--------|--|-------|------|------|
| Falameter | | | Condition | Min. | Max. | Unit |
| Input Leakage Current | | Sili | $0 \text{ V} \leq V_{\text{IN}} \leq V_{\text{CC}}$ | -10 | 10 | μA |
| Output Leakage Current | | SILO | $0 \text{ V} \leq \text{V}_{\text{OUT}} \leq \text{V}_{\text{CC}}$ | -10 | 10 | μA |
| Output Low Voltage | *1 | SVOL | IoL = 3.0 mA | | 0.4 | V |

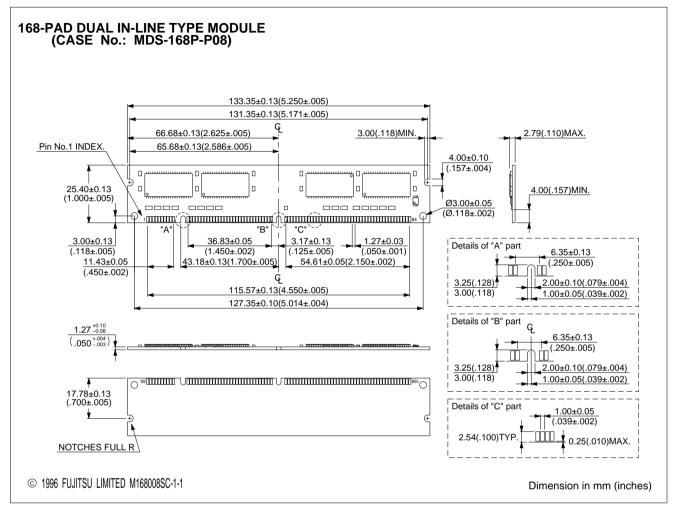
Note: *1. Referenced to Vss.

5. AC CHARACTERISTICS

| No. | Parameter | Symbol | Value | | 11:::4 |
|-----|---|---------|-------|------|--------|
| | Farameter | | Min. | Max. | - Unit |
| 1 | SCL Clock Frequency | fscL | 0 | 100 | KHz |
| 2 | Noise Suppression Time Constant at SCL, SDA Inputs | Tı | | 100 | ns |
| 3 | SCL Low to SDA Data Out Valid | taa | | 3.5 | μs |
| 4 | Time the Bus Must Be Free Before a New Transmission Can Start | tBUF | 4.7 | _ | μs |
| 5 | Start Condition Hold Time | thd:sta | 4.0 | | μs |
| 6 | Clock Low Period | tLow | 4.7 | | μs |
| 7 | Clock High Period | tніgн | 4.0 | _ | μs |
| 8 | Start Condition Set Up Time | tsu:sta | 4.7 | | μs |
| 9 | Data In Hold Time | thd:dat | 0 | | μs |
| 10 | Data In Set Up Time | tsu:dat | 250 | | ns |
| 11 | SDA and SCL Rise Time | tR | _ | 1 | μs |
| 12 | SDA and SCL Fall Time | t⊧ | _ | 300 | ns |
| 13 | Stop Condition Set Up Time | tsu:sto | 4.7 | _ | μs |
| 14 | Data Out Hold Time | tон | 100 | _ | ns |
| 15 | Write Cycle Time | twr | — | 15 | ms |



PACKAGE DIMENSION



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